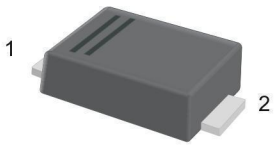
S1AF–TN~S1MF–TN
Surface Mount General Purpose Silicon Rectifiers

Features

- For surface mount applications
- Glass passivated chip junction
- Low profile package
- Easy to pick and place

SMAF



1.Cathode — 2.Anode

Marking Code:
S1AF–TN: S1A
S1BF–TN:S1B
S1DF–TN: S1D
S1GF–TN:S1G
S1JF–TN: S1J
S1KF–TN: S1K
S1MF–TN: S1M

Maximum Ratings and Electrical Characteristics

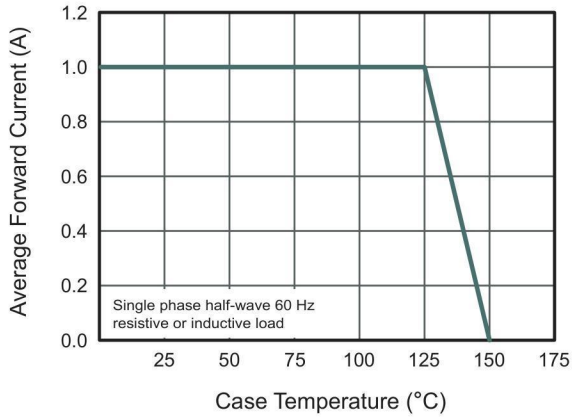
Ratings at 25℃ ambient temperature unless otherwise specified. Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

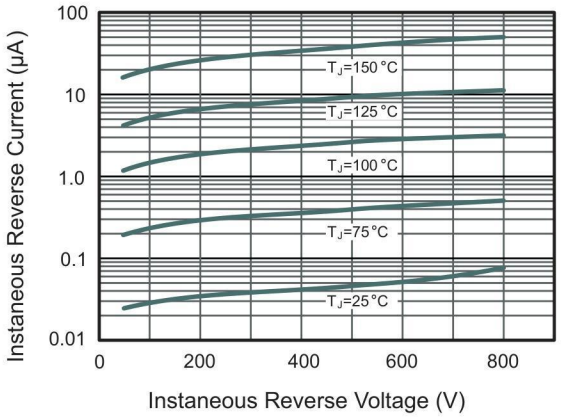
Parameter	Symbols	S1AF–TN	S1BF–TN	S1DF–TN	S1GF–TN	S1JF–TN	S1KF–TN	S1MF–TN	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at T_C=125 °C	$I_{F(AV)}$	1.0							A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	I_{FSM}	30							A
Maximum Instantaneous Forward Voltage at 1 A	V_F	1.1							V
Maximum DC Reverse Current at Rated DC Blocking Voltage T_A = 25 °C T_A = 125 °C	I_R	5 100							μA
Typical Junction Capacitance Note1	C_j	15							pF
Typical Thermal Resistance Note2	$R_{\theta JA}$ $R_{\theta JC}$	80 27							°C/W
Junction Temperature	T_J	150							°C
Storage Temperature Range	T_{STG}	-55 to +150							°C

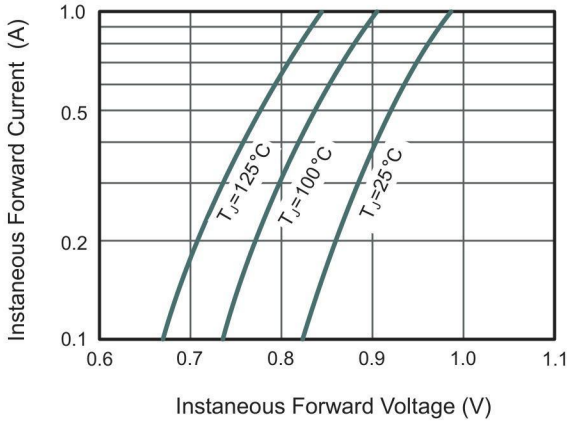
Note:

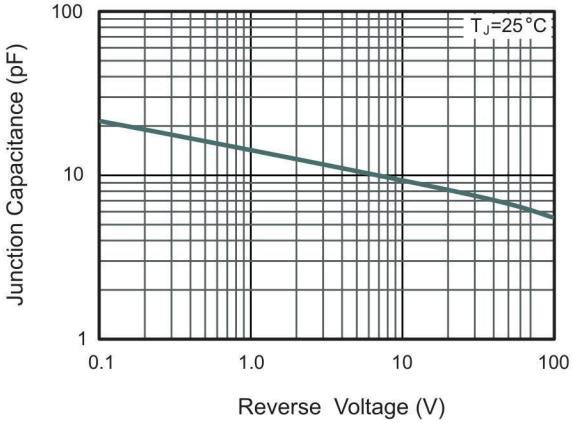
1. Measured at 1 MHz and applied reverse voltage of 4 V DC.
2. P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.

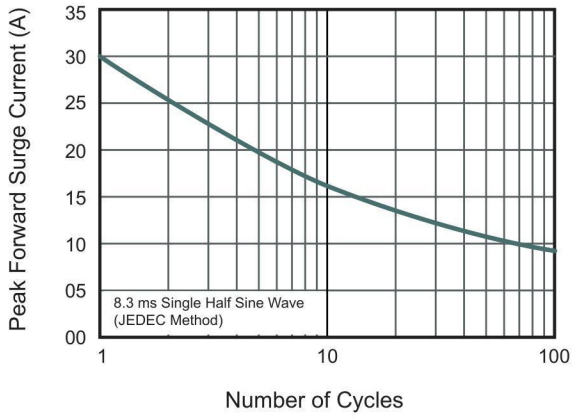
Typical Characteristic Curves







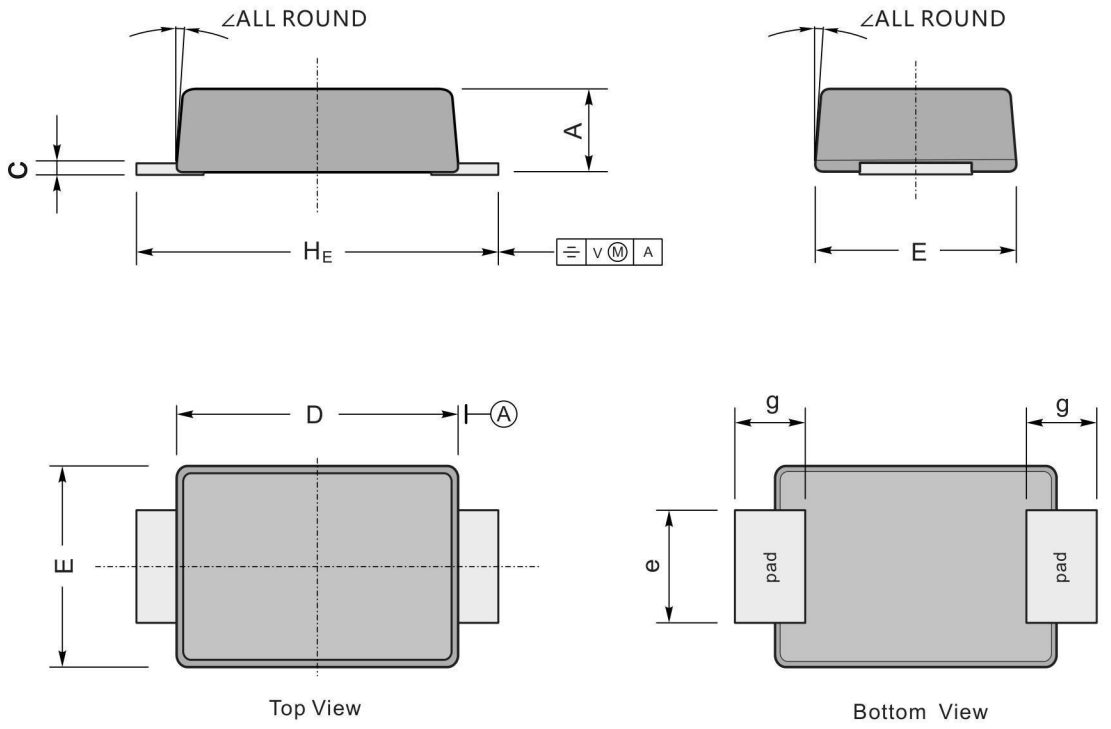




Package Outline

SMAF

Dimensions in mm



UNIT		A	C	D	E	e	g	H_E	∠
mm	max	1.2	0.20	3.7	2.7	1.6	1.2	4.9	7°
	min	0.9	0.12	3.3	2.4	1.3	0.8	4.4	
mil	max	47	7.9	146	106	63	47	193	
	min	35	4.7	130	94	51	31	173	